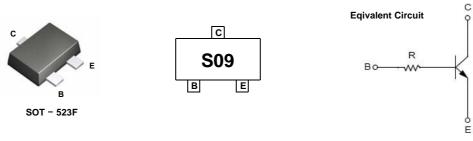


November 2006

# FJY3009R NPN Epitaxial Silicon Transistor

## **Features**

- · Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R=4.7KΩ)
- Complement to FJY4009R



# Absolute Maximum Ratings \* Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	\ \ \
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	100	mA
T <sub>STG</sub>	Storage Temperature Range	-55~150	°C
T <sub>J</sub>	Junction Temperature	150	°C
P <sub>C</sub>	Collector Power Dissipation, by $R_{\theta JA}$	200	mW

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

## Thermal Characteristics\* Ta=25°C unless otherwise noted

Symbol Parameter	IVIAA	Offics	
R <sub>θJA</sub> Thermal Resistance, Junction to Ambient	600	°C/W	

<sup>\*</sup> Minimum land pad size.

## **Electrical Characteristics\*** $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Тур	MAX	Units
V <sub>(BR)</sub> CBO	Collector-Emitter Breakdown Voltage	Ic = 100 uA, IE = 0	40			V
V <sub>(BR)CEO</sub>	Collector-Base Breakdown Voltage	Ic = 1mA, I <sub>B</sub> = 0	40			V
Ісво	Collector-Cutoff Current	Vcb = 30 V, IE = 0			0.1	uA
hfE	DC Current Gain	VcE = 5 V, Ic = 1 mA	100		600	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	Ic = 10 mA, I <sub>B</sub> = 1 mA			0.3	V
fτ	Current Gain - Bandwidth Product	VcE = 10V, Ic = 5 mA		250		MHz
Ccb	Output Capacitance	VcB = 10 V, IE = 0, f = 1.0 MHz		3.7		pF
R	Input Resistor		3.2	4.7	6.2	ΚΩ

<sup>\*</sup> Pulse Test: PW≤300μs, Duty Cycle≤2%

## **Typical Performance Characteristics**

Figure 1. DC current Gain

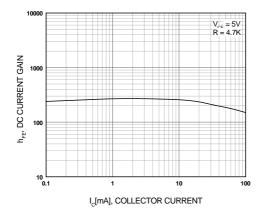


Figure 2. Collector-Emitter Saturation Voltage

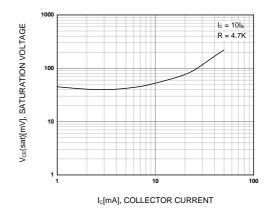
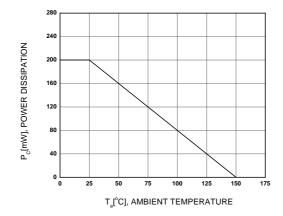
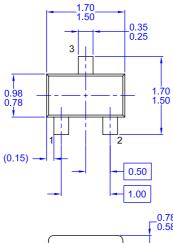


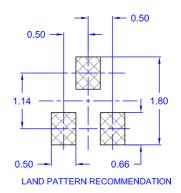
Figure 3. Power Derating

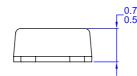


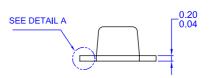
# **Package Dimensions**

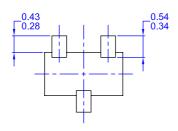
## **SOT-523F**

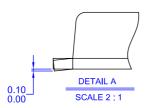












FJY3009R Rev. A

- NOTES: UNLESS OTHERWISE SPECIFIED A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
  C) DIMENSIONS ARE EXCLUSIVE OF BURRS,
  MOLD FLASH, AND TIE BAR EXTRUSIONS.

Dimensions in Millimeters



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